Supporting Information

Substrate Placement Angle-Dependent Growth of Dandelion-like TiO₂ Nanorods for Solid-State Semiconductor-Sensitized Solar Cells

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Figure S1. (a) Placement of substrates at an angle of 15 degrees with respect to the base of the autoclave. (b) Cross-sectional SEM image of TiO₂ NRs grown on FTO glass coated with TiO₂ nanoparticle layer at a substrate placement angle of 15 degrees (NR-TiO₂-FTO). (c) Top-view SEM image of NR-TiO₂-FTO.

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Figure S2. SEM images obtained by increasing the growth time to 8 hours using FTO glass coated with TiO_2 nanoparticle layer as substrate. The substrates placement angle

is 15 degrees with respect to the base of the autoclave. The amount of titanium (IV) butoxide was slightly increased to 0.75 ml to insure there was always enough titanium (IV) butoxide during the growth duration. (a) Crose-ssional SEM image. (b) Top-view SEM image. The SEM images showed that, although the width and length of the nanorods almost doubled and fusion degree got more serious, there were no
dandelion-like TiO₂ clusters observed in this occasion.



Figure S3. Raman spectrum of as-prepared dandelion-like TiO₂ NRs on bare FTO substrates.



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Figure S4. Digital pictures of Sb₂S₃-NR-FTO(1h), Sb₂S₃-NR-FTO(2h) and Sb₂S₃-NR-FTO(3h).



Figure S5. Raman spectrum of Sb₂S₃-NR-FTO(2h)



5 Figure S6. Cross-sectional SEM image of the photovoltaic device using Sb₂S₃-NR-FTO(2h).



Figure S7. Data obtained via using TiO₂ NRs synthesized on bare FTO at placement angle of 15°. The Sb₂S₃ deposition time is 2 h. (a) Cross-sectional SEM image of
5 Sb₂S₃-NR-FTO(2h). (b) Cross-sectional SEM image of the SSSC using Sb₂S₃-NR-FTO(2h). (c) *J-V* characteristics of such SSSC using Sb₂S₃-NR-FTO(2h).